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- [5] US 5,914,893
- [6] US 5,896,312
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- [10] US 6,418,049
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## List of reference symbols

100	First experimentation arrangement
101	Platinum substrate
102	Silver sulfide tip
103	First voltage
104	Quantum point contact
110	Second experimentation arrangement
111	Second voltage
200	Graph
201	Abscissa
202	Ordinate
300	Layer sequence
301	Silicon substrate
302	Silicon oxide layer
303	Photoresist
304	Gold material
305	Trench
310	Layer sequence
311	Gold electrode
312	SAM layer
313	Chalcogenide electrode
320	Layer sequence
321	Cavity
330	Layer sequence
400	Memory cell arrangement
401	Gold bit lines
402	Chalcogenide word lines
500	Memory cell
501	First electrode
502	Second electrode
503	Cavity
504	First source/drain region
505	Second source/drain region
506	Surrounded gate region
600	Memory cell
601	First chalcogenide electrode
602	Second chalcogenide electrode

603 Silver electrode

604 Bridging structure